Contribution ID: **477** Type: **Poster Presentation**

Heat treatment of 6H-Silicon Carbide implanted with palladium at room temperature

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Abstract content
   (Max 300 words)

The Rutherford Backscattering Spectrometry (RBS) and Scanning Electron Microscopy (SEM) were used to investigate the effects of heat treatment of 6H-Silicon Carbide (6H-SiC) implanted with palladium (Pd) ions at a fluency of 2 x 10¹⁶ ions /cm² at room temperature. The implanted samples were then isochronally annealed for a period of 5 hour at a temperature range of 1000℃ to 1400℃. The depth profile of the implanted samples before and after annealing was obtained using RBS. The microstructure and the topography of the samples were also investigated using the scanning electron microscopy (SEM) in order to investigate the effects of implanting the ions and annealing.

Apply to be
 consider for a student
   award (Yes / No)?

Yes

Level for award
 (Hons, MSc,
   PhD)?

MSc

Main supervisor (name and email)
and his / her institution

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Would you like to <br> submit a short paper <br> for the Conference
 Proceedings (Yes / No)?

No

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